

Amendments to the Claims

Claims 1-50 (Cancelled).

51. (Currently amended) A method of forming a bottom-gated thin film transistor comprising the following steps:

forming a transistor gate;

forming a polycrystalline thin film transistor layer over the transistor gate;

forming a fluorine-containing layer proximate the polycrystalline thin film transistor layer, the fluorine-containing layer comprising tungsten; and

transferring fluorine into the polycrystalline thin film transistor layer from the fluorine-containing layer, the transferred fluorine passivating the polycrystalline thin film transistor layer; and

incorporating the passivated polycrystalline thin film transistor layer in the into a bottom-gated thin film transistor construction.

52. (Previously presented) The method of claim 51 wherein the polycrystalline thin film transistor layer comprises silicon.

53. (Previously presented) The method of claim 51 wherein the forming a fluorine-containing layer comprises chemical vapor deposition utilizing WF₆ and SiH₄ precursors.

54. (Previously presented) The method of claim 53 further comprising, after the transferring fluorine, removing the fluorine-containing layer from over the thin film transistor layer.

55. (Currently amended) A method of forming a bottom-gated thin film transistor comprising the following steps:

forming a transistor gate;

forming a polycrystalline thin film transistor layer over the transistor gate;

forming a fluorine-containing layer over the transistor gate and over the polycrystalline thin film transistor layer;

providing a buffering layer intermediate the thin film transistor layer and the fluorine-containing layer; and

transferring fluorine into the polycrystalline thin film transistor layer over the transistor gate from the fluorine-containing layer. layer;

incorporating the poly-crystalline thin film transistor layer into a bottom-gated transistor construction; and

retaining fluorine within the polycrystalline thin film transistor layer in the bottom-gated thin film transistor construction.

56. (Previously presented) The method of claim 55 wherein the fluorine-containing layer comprises tungsten.

57. (Previously presented) The method of claim 55 wherein the buffering layer comprises SiO₂.

58. (Previously presented) The method of claim 55 wherein the polycrystalline thin film transistor layer comprises germanium.